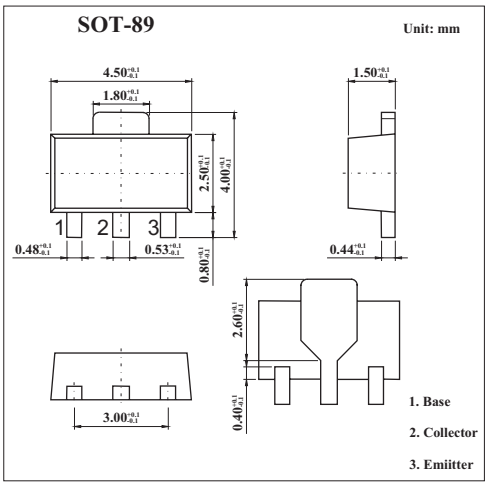
Low Frequency Transistor

2SD2150



■ Features

- Low $V_{CE(sat)}$.
- Excellent DC current gain characteristics.
- NPN silicon transistor.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	40	V
Collector-emitter voltage	V_{CEO}	20	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	3	A
Collector power dissipation	P_C	0.5	W
Junction temperature	Tj	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	I_C=50μA	40			V
Collector-emitter breakdown voltage	BV_{CEO}	I_C=1mA	20			V
Emitter-base breakdown voltage	BV_{EBO}	I_E=50μA	6			V
Collector cutoff current	I_{CBO}	V_{CB}=30V			0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB}=5V			0.1	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=2A, I_B=0.1A		0.2	0.5	V
DC current transfer ratio	h_{FE}	V_{CE}=2V, I_C=0.1A	180		560	
Output capacitance	f_T	V_{CE}=2V, I_E= -0.5A, f=100MHz		290		MHz
Transition frequency	C_{ob}	V_{CB}=10V, I_E=0A, f=1MHz		25		pF

■ h_{FE} Classification

Marking	CF	
Rank	R	S
hFE	180～390	270～560